

BASiC

B1D06065KF

MGT **A** Manufacturer Group of Technology

650V 🛦 6A 🛦 SIC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ THT type Excellent surge capability Easy paralleling due to positive V_F temperature coefficient Temperature independent switching Low forward voltage

TO-220F-2L package ▲ Electrical insulated mounting tab

SPECIFICATION

Item (T _c = 25°C, unless otherwise noted)	Characteristics	
Operating Temperature Range	TJ	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	V _{RRM}	650V
Continuous Forward Current at T _c = 145°C	I _F	6A
Total Capacitive Charge (TJ = 25°C)	Qc	17nC
Capacitance Stored Energy (V _R = 400V)	Ec	4.5µJ
Diode Forward Voltage (T _J = 175° C, I _F = 6A)	V _F	1.73V
Power Dissipation	Ρ _{τοτ}	53W

RoHS

REACH

HALOGEN

FREE

APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
∳∿⊧	0		PFC	*		

PIN DESCRIPTION

Circuit Diagram	Outline • Front View	Pin No.	Description
		1 2	Cathode Anode

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ABSOLUT MAXIMUM RATINGS **A** T_c = 25°C, unless otherwise noted

ltem	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		V _{RRM}	650	V
Non-Repetitive Peak Reverse Voltage		V _{RSM}	650	V
Continuous Forward Current	T _C = 25°C	I _F	16	А
Continuous Forward Current	T _C = 145°C	I _F	6	А
Non-Repetitive Forward Surge Current	T_{C} = 25°C, t_{p} = 10ms, Half Sine Wave	I _{FSM}	45	А
I ² t Value	T _c = 25°C, t _p = 10ms	∫i²dt	10.12	A ² s
Power Dissipation	T _C = 25°C	P _{TOT}	53	W
Power Dissipation	T _C = 110°C	P _{TOT}	23	W
Operating Junction Temperature		TJ	-55 to +175	°C
Storage Temperature Range		T _{STG}	-55 to +175	°C
TO-220 Mounting Torque	M3 Screw		0.7	Nm

ELECTRICAL CHARACTERISTICS

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T _J = 25°C	V _{DC}	650			V
Diode Forward Voltage	I _F = 6A, T _J = 25°C	V _F		1.43		V
Diode Forward Voltage	I _F = 6A, T _J = 175°C	VF		1.73		V
Reverse Current	$V_R = 650V, T_J = 25^{\circ}C$	I _R		1		μA
Reverse Current	V _R = 650V, T _J = 175°C	I _R		20		μA
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics						
	$V_{R} = 400V, T_{J} = 25^{\circ}C$					
Total Capacitive Charge	$Q_C = \int_0^{V_R} C(V) dV$	Q _C		17		nC
Total Capacitance	$V_{R} = 1V$, f = 1MHz, T _J = 25°C	С		271		рF
Total Capacitance	V_{R} = 300V, f = 1MHz, T _J = 25°C	С		30.1		рF
Total Capacitance	V _R = 600V, f = 1MHz, T _J = 25°C	С		29.8		pF
Capacitance Stored Energy	V _R = 400V, T _J = 25°C	Ec		4.5		μ

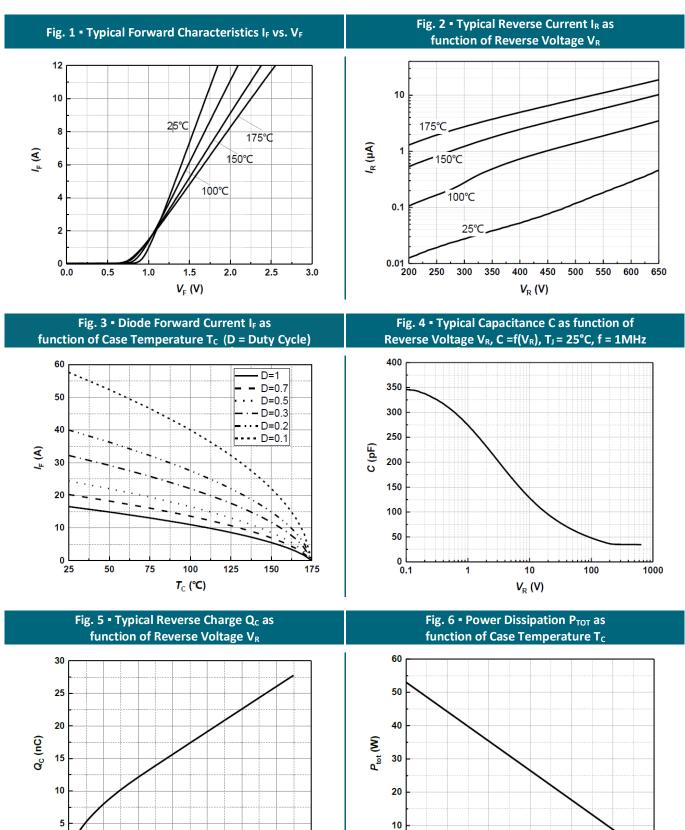
THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		2.810		K/W

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REFERENCE DATA A TYPICAL PERFORMANCE



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V_R (V)

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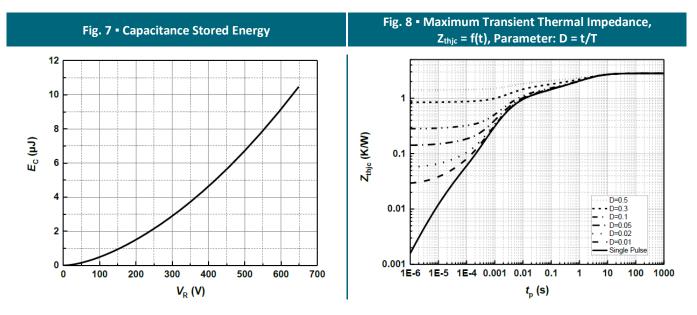
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T_C (℃)

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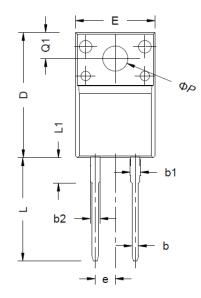


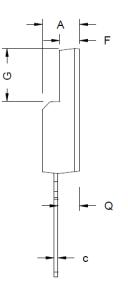
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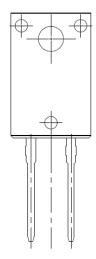




PACKAGE OUTLINE







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Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.60	4.70	4.80	F	2.44	2.54	2.64
b	0.70	0.80	0.91	G	6.50	6.70	6.90
b1	1.20	1.30	1.47	L	12.90	13.10	13.30
b2	1.10	1.20	1.30	L	12.70	-	13.70
С	0.45	0.50	0.63	L1	3.13	3.23	3.33
D	15.80	15.87	15.97	Q	2.65	2.75	2.85
D	15.15	15.45	15.75	Q1	3.20	3.30	3.40
е		2.54 BSC		ØР	2.08	3.18	3.28
E	10.00	10.10	10.30				

TO-220F-2L package ▲ Epoxy meets UL94-V0

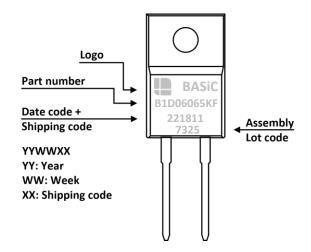
ORDERING INFORMATION

Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
B1D06065KF	TO-220F-2L	Tube	50pcs	500pcs	5,000pcs

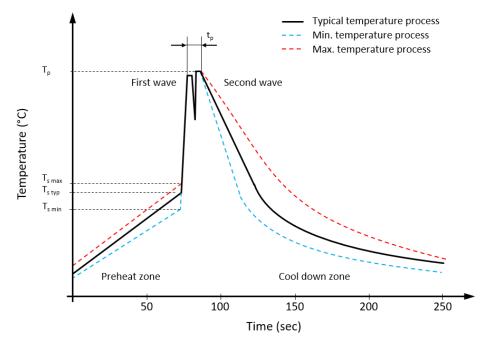
SILICON CARBIDE (SiC) SCHOTTKY DIODE ▲ B1D06065KF

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PART MARKING



RECOMMENDED WAVE SOLDERING PROFILE ▲ THT PACKAGE



Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value 🛦 Sn-Pb Assembly	Value A Pb-free Assembly
Preheat temperature min.	T_{smin}	100 °C	100 °C
Preheat temperature typical	T _{s typ}	120 °C	120 °C
Preheat temperature max.	$T_{s max}$	130 °C	130 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	70 seconds	70 seconds
Peak temperature	Tp	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	t _p	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes
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REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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